

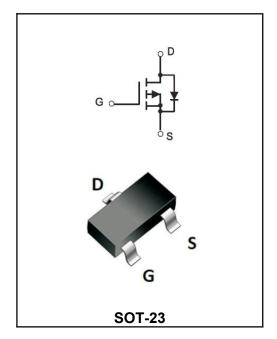
-60V P-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

I _D	-2.8A
V _{DSS}	-60V
R _{DSON} -typ(@V _{GS} =-10V)	< 200mΩ (Type:165 mΩ)

Application

- **♦**Battery protection
- **♦**Load switch
- ♦Uninterruptible power supply



Marking Code				
YFW3P06B	3P06			

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V _{DS}	-60	V
Gate - Source Voltage	V _{GS}	±20	V
Continuous Drain Current, V _{GS} @ -10V ¹ @T _A =25℃	I _D	-2.8	Α
Continuous Drain Current, V _{GS} @ -10V ¹ @T _A =70 °C	I _D	-1.8	Α
Pulsed Drain Current ²	Ірм	-8.4	Α
Total Power Dissipation³@T _A =25°C	PD	1.5	w
Storage Temperature Range	T _{STG}	-55 to +150	°C
Operating Junction Temperature Range	TJ	-55 to +150	°C
Thermal Resistance Junction-Ambient ¹	R _{0JA}	125	°C/W
Thermal Resistance Junction-Case ¹	R _{0JC}	80	°C/W

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Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Тур	Max -	Units V
Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	BV _{DSS}	-60	-67		
BVDSS Temperature Coefficient	Reference to 25℃, I _D =-1mA	∆BV _{DSS/∆TJ}	-	-0.021	-	V/°C
Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-1.5A	Б	-	165	200	mΩ
	V _{GS} =-4.5V, I _D =-1A	R _{DS(ON)}	-	200	250	
Gate -Threshold Voltage	V V I 050 A	V _{GS(th)}	-1.0	1.7	-2.5	V
√ _{GS} (th) Temperature Coefficient	$V_{DS}=V_{GS}$, $I_D=-250uA$	△V _{GS(th)}	-	4.08	-	mV/°C
Duraina Carriara Laraka na Carriara	V _{DS} =-48V , V _{GS} =0V , T _J =25℃		-	-	1	- μΑ
Orain -Source Leakage Current	V _{DS} =-48V , V _{GS} =0V , T _J =55°C	l _{DSS}	-	-	5	
Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	I _{GSS}	-	-	±100	nA
Forward Transconductance	V _{DS} =-5V, I _D =-1.5A	g _{FS}	-	5.9	-	S
Fotal Gate Charge(-4.5V)	\/ - 20\/	Qg	-	4.6	-	
Gate-Source Charge	V _{DS} =-20V V _{GS} =-4.5V	Q _{gs}	-	1.4	-	nC
Gate-Drain Charge	- I _D =-1.5A	Q _{gd}	-	1.62	-	1
Turn-on delay time		t _{d(on)}	-	17.4	-	
Rise Time	V_{DD} =-15V V_{GS} =-10V	T _r	-	5.4	-	
Furn-Off Delay Time	$R_G=3.3\Omega$ $I_D=-1A$	t _{d(OFF)}	-	37.2	-	- nS
Fall Time	ID=-1A	t _f	-	2.4	-	1
nput Capacitance	\/ - 45\/	C _{iss}	-	531	-	
Output Capacitance	V _{DS} =-15V V _{GS} =0V	Coss	-	59	-	PF
Reverse Transfer Capacitance	f=1.0MHz	C _{rss}	-	38	-	1
Continuous Source Current ^{1.4}		Is	-	-	-1.7	Α
Pulsed Source Current ^{2.4}	V _G =V _D =0V , Force Current	I _{SM}	-	-	-7	Α
Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25℃	V _{SD}	-	-	-1.2	V

Note:

- 1. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
- 2. The data tested by pulsed , pulse width $\leq 300 \text{us}$, duty cycle $\leq 2\%$
- $3 {\scriptstyle \smallsetminus}$ The power dissipation is limited by $150 {\, ^\circ \! \rm C}$ junction temperature
- 4. The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation.

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Rev:BDYK



Ratings and Characteristic Curves

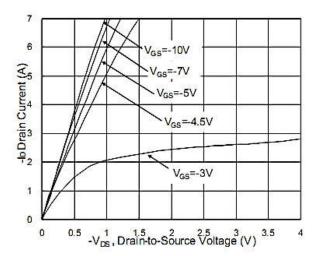


Fig.1 Typical Output Characteristics

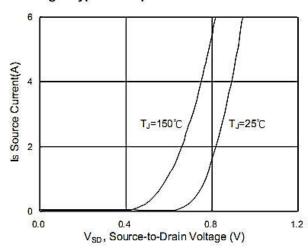


Fig.3 Forward Characteristics Of Reverse

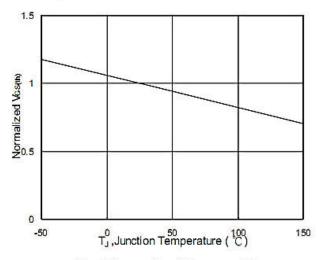


Fig.5 Normalized V_{GS(th)} v.s T_J

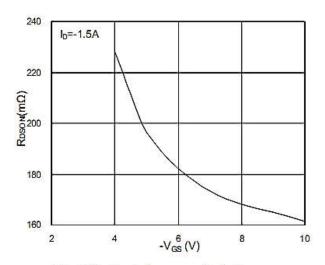


Fig.2 On-Resistance v.s Gate-Source

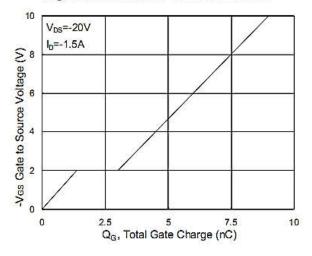


Fig.4 Gate-Charge Characteristics

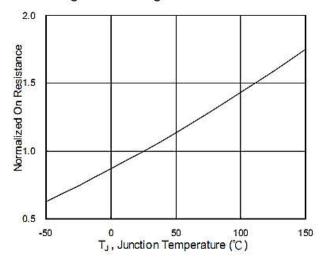
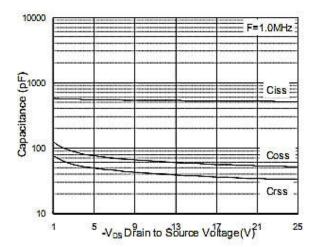


Fig.6 Normalized Roson v.s TJ



Ratings and Characteristic Curves



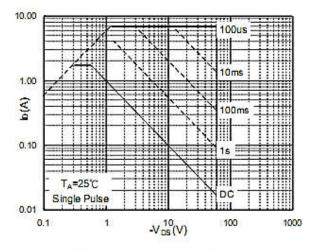


Fig.7 Capacitance

Fig.8 Safe Operating Area

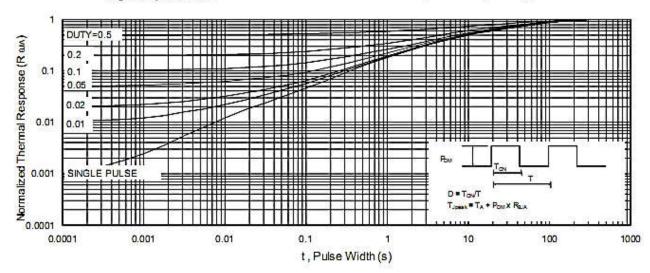
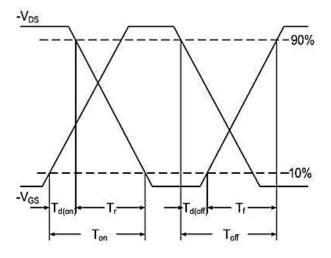


Fig.9 Normalized Maximum Transient Thermal Impedance



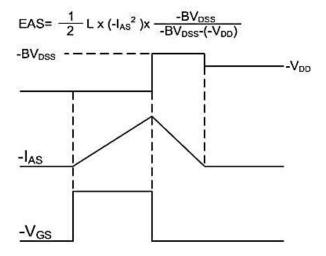


Fig.11 Unclamped Inductive Waveform

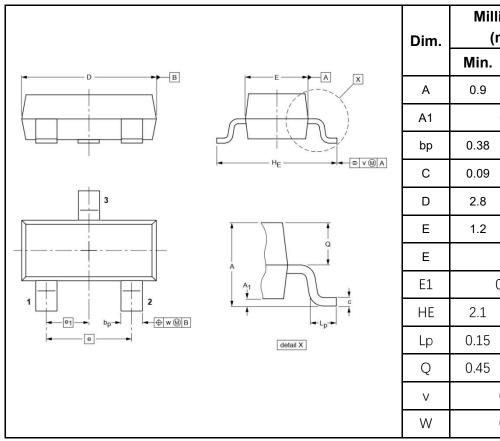


Ordering information

Package	Rage Packing Description		Packing Quantity
SOT-23	Tape/Reel,7"reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

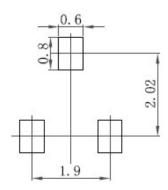
Package Dimensions

SOT-23



Dim.	Millimeter (mm)		mil		
	Min.	Min. Max.		Max.	
Α	0.9	1.15	35	45	
A1	0	.1	3.9)	
bp	0.38	0.48	15	19	
С	0.09	0.15	3.54	5.9	
D	2.8	3.0	110	118	
Е	1.2	1.4	47	55	
Е	1.9		75		
E1	0.95		37		
HE	2.1	2.55	83	100	
Lp	0.15	0.45	5.9	18	
Q	0.45	0.55	18	22	
V	0.2		7.9		
W	0.1		4		

The recommended mounting pad size





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